The RF Line **UHF Linear Power Transistor**

 \dots designed for very high output 1.5 V MATV amplifiers up to 860 MHz and 500 mW Band V TV transposer stages. Gold metallization and diffused emitter ballast resistors are used to enhanced reliability, ruggedness and linearity.

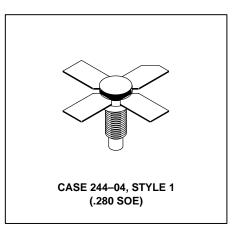
- Band IV and V (470-860 MHz)
- 0.5 W Pref @ -58 dB IMD
- High Gain 12 dB Typ, Class A, f = 860 MHz
- · Gold Metallization for Reliability

TPV596A

0.5 W, 470-860 MHz UHF LINEAR POWER TRANSISTOR

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|------------------|--------------|---------------|
| Collector–Emitter Voltage | VCEO | 24 | Vdc |
| Collector–Base Voltage | VCBO | 45 | Vdc |
| Emitter–Base Voltage | V _{EBO} | 3.5 | Vdc |
| Collector Current — Continuous | IC | 0.7 | Adc |
| Total Device Dissipation @ T _C = 25°C Derate above 25°C | PD | 8.75 0.05 | Watts W/°C |
| Operating Junction Temperature | TJ | 200 | °C |
| Storage Temperature Range | T _{stg} | -65 to +200 | °C |



THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|-----------------|-----|------|
| Thermal Resistance, Junction to Case (T _C = 70°C) | $R_{\theta JC}$ | 20 | °C/W |

ELECTRICAL CHARACTERISTICS

| Characteristic | Symbol | Min | Тур | Max | Unit |
|--|------------------|-----|-----|------|------|
| OFF CHARACTERISTICS | | | | | |
| Collector–Emitter Breakdown Voltage (I _C = 20 mA, I _B = 0) | V(BR)CEO | 24 | _ | _ | Vdc |
| Collector–Base Breakdown Voltage (IC = 1.0 mA, IE = 0) | V(BR)CBO | 45 | _ | _ | Vdc |
| Emitter–Base Breakdown Voltage (I _E = 4.0 mA, I _C = 0) | V(BR)EBO | 3.5 | _ | _ | Vdc |
| Emitter–Base Leakage Current (V _{EB} = 2.0 V) | I _{EBO} | _ | _ | 0.25 | mA |
| Collector Cutoff Current (V _{CB} = 28 V, I _E = 0) | I _{CBO} | _ | _ | 1.0 | mAdc |
| Collector–Emitter Breakdown Voltage (IC = 20 mA, RBE = 10 Ω) | V(BR)CER | 50 | _ | _ | Vdc |
| ON CHARACTERISTICS | | | | | |
| DC Current Gain (I _C = 100 mA, V _{CE} = 5.0 V) | hFE | 15 | _ | 120 | _ |
| DYNAMIC CHARACTERISTICS | | | | | |
| Output Capacitance (V _{CB} = 28 V, I _E = 0, f = 1.0 MHz) | C _{ob} | _ | _ | 5.0 | pF |

(continued)



ELECTRICAL CHARACTERISTICS — continued

| Characteristic | Symbol | Min | Тур | Max | Unit |
|---|------------------|--------------------------------|-----|-----|------|
| FUNCTIONAL TESTS | | | | | |
| Common–Emitter Amplifier Power Gain (VCE = 20 V, Pout = 0.5 W, f = 860 MHz, IE = 0.22 A) | G _{PE} | 11.5 | 12 | _ | dB |
| Load Mismatch (VCE = 20 V, Pout = 1.0 W, IE = 0.22 A, f = 860 MHz, Load VSWR = ∞ :1, All Phase Angles) | Ψ | No Degradation in Output Power | | | ver |
| Intermodulation Distortion, 3 Tone (f = 860 MHz, V _{CE} = 20 V, I _E = 0.22 A, P _{ref} = 1.0 W, Vision Carrier = -8.0 dB, Sound Carrier = -7.0 dB, Sideband Signal = -16 dB, Specification TV05001) | IMD ₁ | _ | _ | -50 | dB |
| Intermodulation Distortion (IDEM) (f = 860 MHz, V _{CE} = 20 V, I _E = 0.22 A, P _{ref} = 0.5 W, Vision Carrier = -8.0 dB, Sound Carrier = -10 dB, Sideband Signal = -16 dB) | IMD ₂ | _ | -60 | -58 | dB |

TYPICAL CHARACTERISTICS

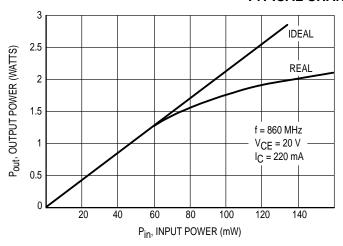


Figure 1. Power Output versus Power Input

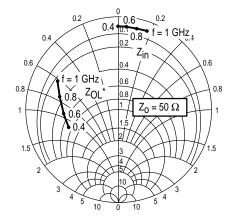


Figure 2. Large Signal Impedances VCE = 20 V — IC = 220 mA

 Z_{OL}^* = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage and frequency.

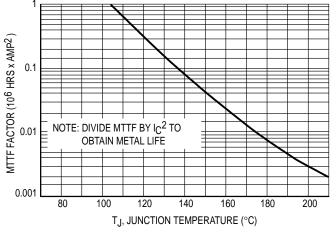


Figure 3. MTTF Factor versus Junction Temperature

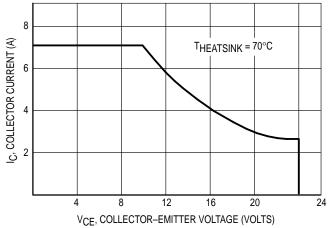
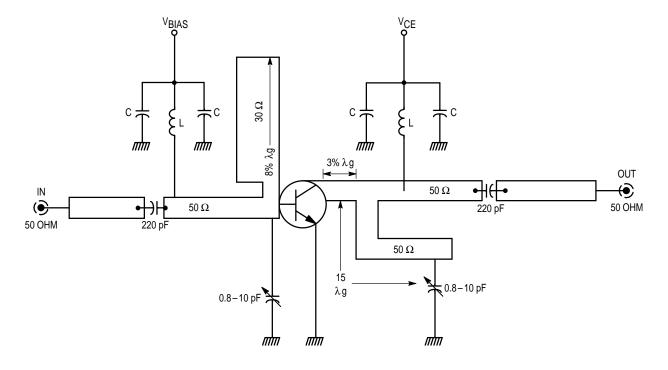


Figure 4. DC Safe Operating Area



NOTE: λg is the wave length in the microstrip circuit

Figure 5. 860 MHz Test Circuit

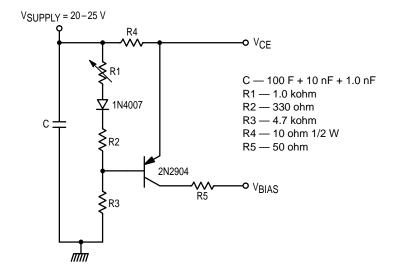
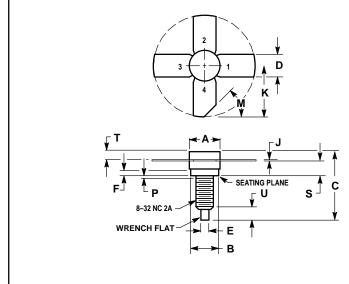


Figure 6. Class A Bias Circuit

PACKAGE DIMENSIONS



| | MILLIN | METERS | INC | HES | |
|-----|--------|--------|--------|-------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 7.06 | 7.26 | 0.278 | 0.286 | |
| В | 6.20 | 6.50 | 0.244 | 0.256 | |
| С | 14.99 | 16.51 | 0.590 | 0.650 | |
| D | 5.46 | 5.96 | 0.215 | 0.235 | |
| E | 1.40 | 1.65 | 0.055 | 0.065 | |
| G | 1.52 | | 0.060 | _ | |
| J | 0.08 | 0.17 | 0.003 | 0.007 | |
| K | 11.05 | | 0.435 | | |
| M | 45° | NOM | 45°NOM | | |
| Р | | 1.27 | | 0.050 | |
| S | 3.00 | 3.25 | 0.118 | 0.128 | |
| T | 1.40 | 1.77 | 0.055 | 0.070 | |
| U | 2.92 | 3.68 | 0.115 | 0.145 | |

STYLE 1: PIN 1. EMITTER

2. BASE

3. EMITTER 4. COLLECTOR

CASE 244-04 ISSUE J

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